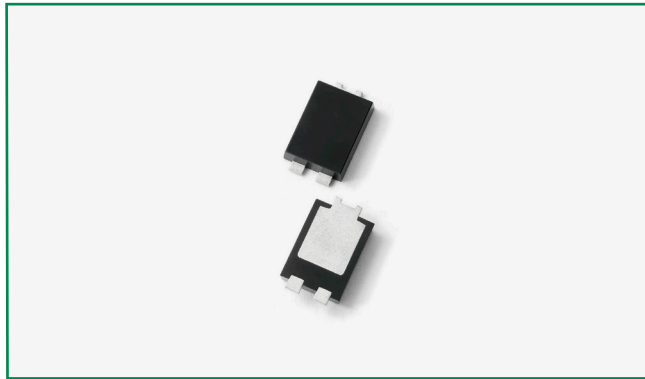


Schottky Barrier Rectifier

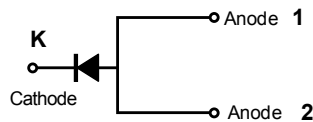
DST8100S-A, 8A, 100V, TO-277B, Single

DST8100S-A

 **AUTOMOTIVE GRADE**  **HF**  **RoHS**  **E3**



Pin out



Description

Littelfuse DST series Ultra Low V_F Schottky Barrier Rectifier is designed to meet the general requirements of automotive applications by providing high temperature, low leakage and lower V_F products.

It is suitable for high frequency switching mode power supply, free-wheeling diodes and polarity protection diodes.

Features

- Hi reliability application and automotive grade AEC-Q101 qualified
- Ultra low forward voltage drop
- High frequency operation
- MSL: Level 1 - unlimited
- High junction temperature capability
- Trench MOS Schottky technology
- Single die in TO-277B Package
- Pb-free E3 means 2nd level interconnect is Pb-free and the terminal finish material is tin(Sn) (IPC/ JEDEC J-STD-609A.01)

Applications

- Switching mode power supply
- DC/DC converters
- Free-Wheeling diodes
- Polarity Protection Diodes

Maximum Ratings

Parameters	Symbol	Test Conditions	Max	Unit
Peak Inverse Voltage	V_{RWM}	-	100	V
Average Forward Current	$I_{F(AV)}$	50% duty cycle @ $T_L = 125^\circ\text{C}$ rectangular wave form	8	A
Peak One Cycle Non-Repetitive Surge Current	I_{FSM}	8.3 ms, half Sine pulse	150	A

Electrical Characteristics

Parameters	Symbol	Test Conditions	Typ	Max	Unit
Forward Voltage Drop*	V_{F1}	@4A, Pulse, $T_J = 25^\circ\text{C}$	0.52	-	V
		@8A, Pulse, $T_J = 25^\circ\text{C}$	0.66	0.68	
	V_{F2}	@4A, Pulse, $T_J = 125^\circ\text{C}$	0.47	-	
		@8A, Pulse, $T_J = 125^\circ\text{C}$	0.58	0.62	
Reverse Current*	I_{R1}	@ $V_R = \text{rated } V_R$, $T_J = 25^\circ\text{C}$	13.5	70	μA
	I_{R2}	@ $V_R = \text{rated } V_R$, $T_J = 125^\circ\text{C}$	3.5	15	mA
Junction Capacitance	C_T	@ $V_R = 5\text{V}$, $T_C = 25^\circ\text{C}$, $f_{SIG} = 1\text{MHz}$	542	-	pF
Voltage Rate of Change	dv/dt		-	10000	V/ μs

* Pulse Width < 300 μs , Duty Cycle < 2%

Schottky Barrier Rectifier

DST8100S-A, 8A, 100V, TO-277B, Single

Thermal-Mechanical Specifications

Parameters	Symbol	Test Conditions	Max	Unit
Junction Temperature	T_J		-55 to +150	°C
Storage Temperature	T_{stg}		-55 to +150	°C
Maximum Thermal Resistance Junction to Ambient	R_{thJA}	DC operation	75	°C/W
Maximum Thermal Resistance Junction to Lead	R_{thJL}		4	°C/W
Approximate Weight	wt		0.08	g
Case Style		TO-277B		

*Lead temperature monitored at the cathode pin

Figure 1: Forward Current Derating Curve

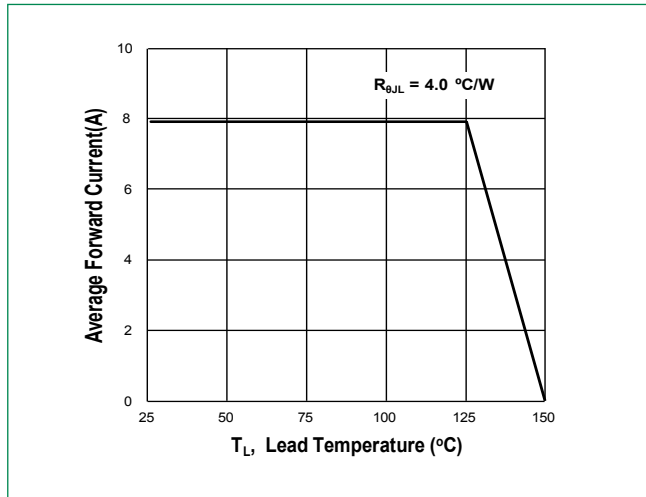


Figure 2: Forward Power Loss Characteristics

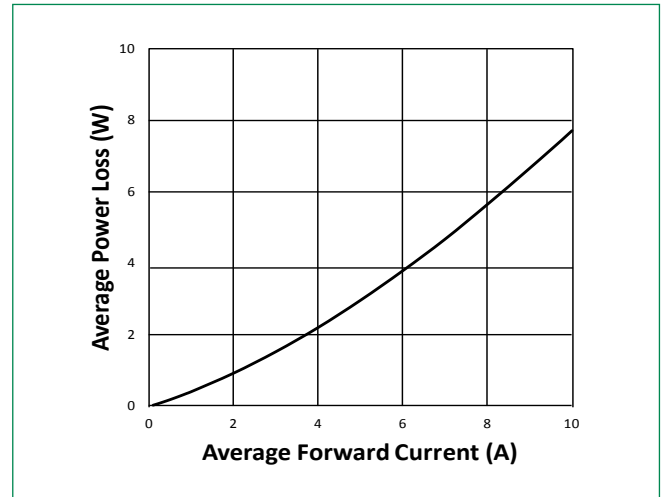


Figure 3: Typical Forward Characteristics

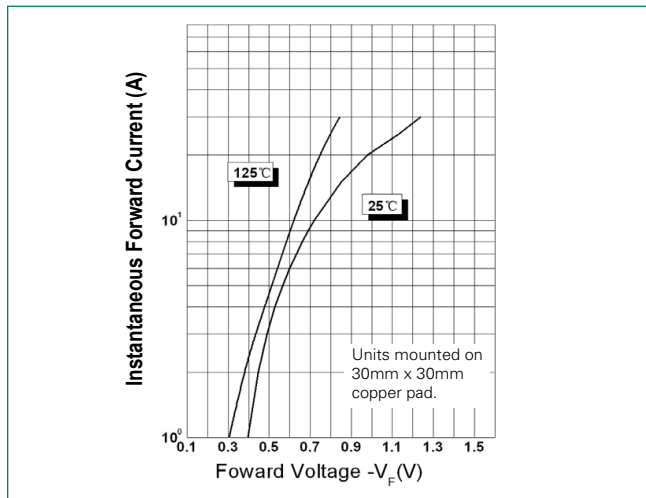


Figure 4: Typical Reverse Characteristics

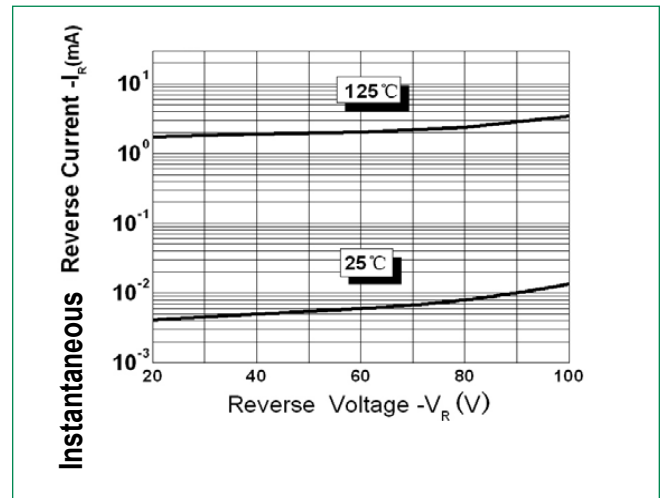
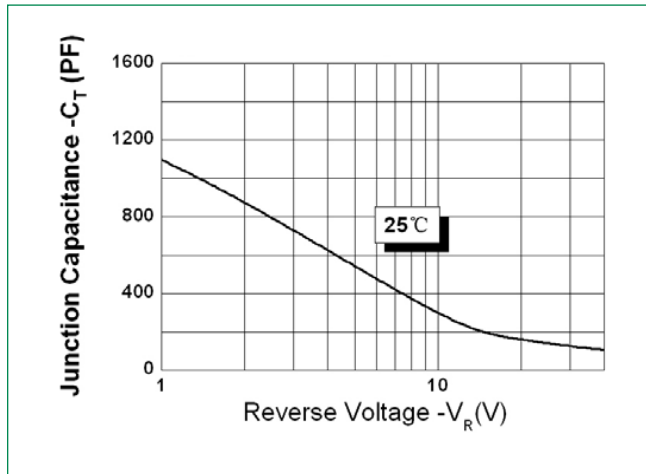
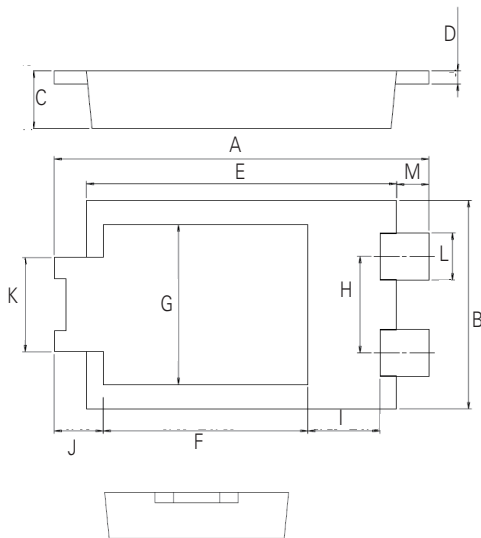


Figure 5: Typical Junction Capacitance

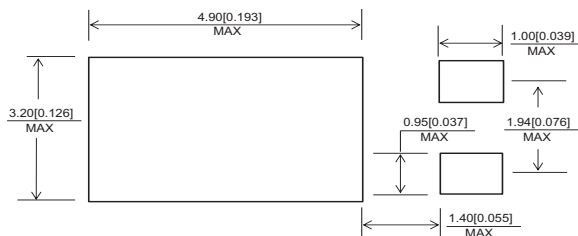


Dimensions-TO-277B

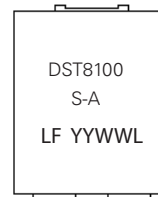


Symbol	Millimeters		
	Min	Typ	Max
A	6.30	6.50	6.70
B	3.88	3.98	4.08
C	0.95	1.10	1.25
D	0.20	0.25	0.30
E	5.28	5.38	5.48
F	3.40	3.55	3.70
G	2.90	3.05	3.20
H	1.74	1.84	1.94
I	1.10	1.25	1.40
J	-	0.85	-
K	1.70	1.80	1.90
L	0.85	0.90	0.95
M	-	0.56	-

Mounting Pad Layout



Part Numbering and Marking System



DST	= Device Type
8	= Forward Current (8A)
100	= Reverse Voltage (100V)
S	= Package Type
A	= AEC-Q101 qualified device
LF	= Littelfuse
YY	= Year
WW	= Week
L	= Lot Number

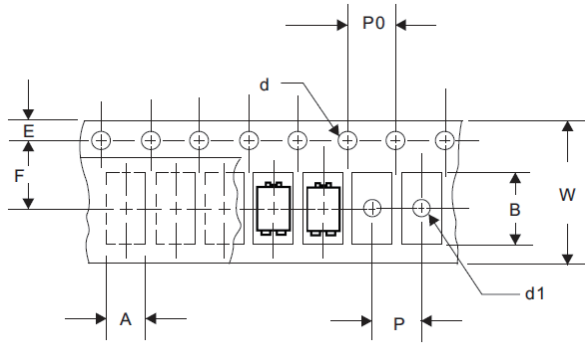
Schottky Barrier Rectifier

DST1040S-A, 10A, 45V, TO-277B, Single

Packing Options

Part Number	Marking	Packing Mode	M.O.Q
DST8100S-A	DST8100S-A	5000pcs / Reel	5000

Carrier Tape & Reel Specification



Symbol	Millimeters	
	Min	Max
A	4.28	4.48
B	6.80	7.00
d	1.40	1.60
d1	-	1.50
E	1.65	1.85
F	5.40	5.60
P	7.90	8.10
P0	3.90	4.10
W	11.70	12.30